255RK SERIES
Power Silicon Controlled Rectifiers
400 Amp RMS SCRs

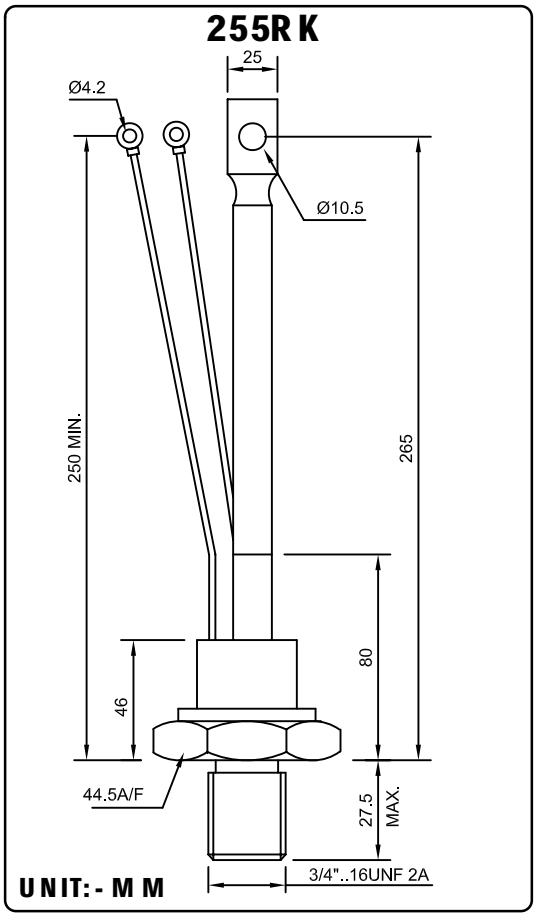
Types : 255RK20 TO 255RK160

FEATURES

- *Centre amplifying gate.*
- *International standard case TO-209AB (TO-118).*
- *Threaded studs UNF 3/4 - 16UNF 2A.*
- *Compression Bonded Encapsulation for heavy duty operations such as severe thermal cycling.*

TYPICAL APPLICATIONS

- *DC motor control (e.g. for machine tools).*
- *Controlled rectifiers (e.g. for battery charging, UPS).*
- *AC controllers (e.g. temperature control, lights control).*



MAJOR RATINGS & CHARACTERISTICS

Parameters		255RK	Units
$I_{T(AV)}$		250	A
	@ T_C	75	°C
$I_{T(RMS)}$		400	A
I_{TSM}	@ 50 Hz	7000	A
I^2t	@ 50 Hz	245	KA^2s
V_{DRM}/V_{RRM}		200 to 1600	V
t_q	typical	100	µs
T_J		-40 to 125	°C

SILICON CONTROLLED RECTIFIERS

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ELECTRICAL SPECIFICATION

VOLTAGE RATINGS

Type Number	Voltage Code	V_{RRM} / V_{DRM} max. repetitive peak and off-state vltage V	V_{RSM} max. non-repetitive peak voltage V	I_{DRM} / I_{RRM} max. @ 125°C mA
255RK	20	200	300	50
	40	400	500	
	60	600	700	
	80	800	900	
	100	1000	1100	
	120	1200	1300	
	140	1400	1500	
	160	1600	1700	

ON-STATE CONDUCTION

	Parameter	255RK	Units	Conditions		
$I_{T(AV)}$	Max. average on-state current	250	A	180° conduction, half sine wave		
	@ case temperature	75	°C			
$I_{T(RMS)}$	Max. RMS on-state current	400	A	DC @ 64 Deg.C case Temp.		
I_{TSM}	Max. peak one cycle non-repetitive surge current	7000		t = 10ms	No voltage reapplied	Sinusoidal half wave, Initial $T_J = T_J$ max.
		5570		t = 10ms	100% V_{RRM} reapplied	
I^2t	Maximum I^2t for fusing	245	kA^2s	t = 10ms	No voltage reapplied	
		155		t = 10ms	100% V_{RRM} reapplied	
I^2t	Maximum I^2t for fusing	2450	kA^2s	t = 0.1 to 10ms. No voltage reapplied.		
$V_{T(TO)1}$	Low level value of threshold voltage	0.98	V	(16.7% x π x $I_{F(AV)}$ < I < π x $I_{F(AV)}$), $T_J = T_J$ max.		
$V_{T(TO)2}$	High level value of threshold voltage	0.99		(π x $I_{F(AV)}$ < I < 20 x π x $I_{F(AV)}$), $T_J = T_J$ max.		
r_{t1}	Low level value of on state slope resistance	0.85	mΩ	(16.7% x π x $I_{F(AV)}$ < I < π x $I_{F(AV)}$), $T_J = T_J$ max.		
r_{t2}	High level value of on state slope resistance	0.83		(π x $I_{F(AV)}$ < I < 20 x π x $I_{F(AV)}$), $T_J = T_J$ max.		
V_{TM}	Max. on state voltage	1.90	V	I_{pk} = 800A, T_J = 125°C, t_p = 10ms sine pulse		
I_H	Maximum holding current	600	mA	T_J = 25°C, anode supply 12V resistive load		
I_L	Latching current	1000				

SWITCHING

	Parameter	255RK	Units	Conditions
di/dt	Max. non-repetitive rate of rise of turned-on current	1000	A/µs	Gate drive 20V, 20Ω, tr ≤ 1 µs T_J = 125°C, anode voltage ≤ 80% V_{DRM}
t_d	Typical delay time	1.0	µs	Gate current 1A, di_g/dt = 1A/µs V_d = 0.67% V_{DRM}, T_J = 25°C
t_q	Typical turn-off time	100		I_{TM} = 550A, T_J = 125°C, di/dt = 40A/µs, V_R = 50V dv/dt = 20V/µs, Gate 0V 100Ω, t_p = 500µs

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BLOCKING

	Parameter	255RK	Units	Conditions
dv/dt	Maximum critical rate of rise of off-state voltage	500	V/µs	T_J = 125°C, linear to 80% rated V_{DRM}
I_{RRM} I_{DRM}	Max. peak reverse and off-state leakage current	50	mA	T_J = 125°C, rated V_{DRM}/V_{RRM} applied

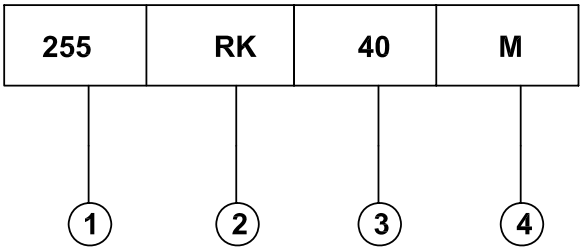
TRIGGERING

	Parameter	255RK		Units	Conditions	
P_{GM}	Maximum peak gate power	10.0		W	T_J = 125°C, $t_p \leq$ 5ms	
$P_{G(AV)}$	Maximum average gate power	2.0			T_J = 125°C, f= 50Hz, d% = 50	
I_{GM}	Max. peak positive gate current	3.0		A	T_J = 125°C, $t_p \leq$ 5ms	
$+V_{GM}$	Max. peak positive gate voltage	20		V	T_J = 125°C, $t_p \leq$ 5ms	
$-V_{GM}$	Max. peak negative gate voltage	5.0				
		TYP.	MAX.			
I_{GT}	DC gate current required to trigger	200 100 50	-- 200 --	mA	T_J = -40°C T_J = 25°C T_J = 125°C	Max. required gate trigger / current / voltage are the lowest value which will trigger all units 12V anode-to-cathode applied.
V_{GT}	DC gate voltage required to trigger	2.5 1.8 1.1	-- 3.0 --	V	T_J = -40°C T_J = 25°C T_J = 125°C	
I_{GD}	DC gate current not to trigger	10		mA	T_J = 125°C	Max. gate current /voltage not to trigger is the max. value which will not trigger any unit with rated V_{DRM} anode-to-cathode applied.
V_{GD}	DC gate voltage not to trigger	0.25		V		

THERMAL AND MECHANICAL SPECIFICATION

	Parameter	255RK	Units	Conditions
T_J	Max. operating temperature range	-40 to 125	°C	
T_{stg}	Max. storage temperature range	-40 to 150		
R_{thJC}	Max. thermal resistance, junction to case	0.105	K/W	DC operation
R_{thCS}	Max. thermal resistance, case to heat sink	0.03		Mounting surface, smooth, flat and greased
T	Mounting torque, ±10%	48.5	Nm	Non lubricated threads
wt	Approximate weight	535	gm	
	Case style	To - 209AE (TO-118)		See outline

ORDER INFORMATION TABLE



(1) - Current Code

(2) - RK - Essential part number

(3) - Voltage Rating (See table)

(4) - None - Stud 3/4" 16UNF 2A Threading
M - Stud M20 x 1.5P Metric Threading

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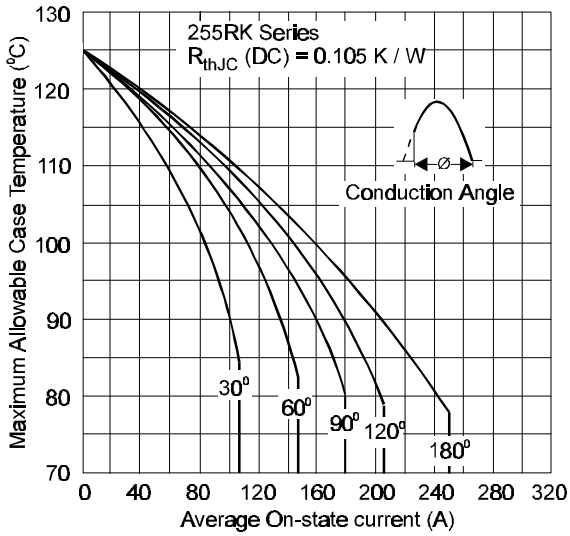

Fig. 1 - Current Ratings Characteristics

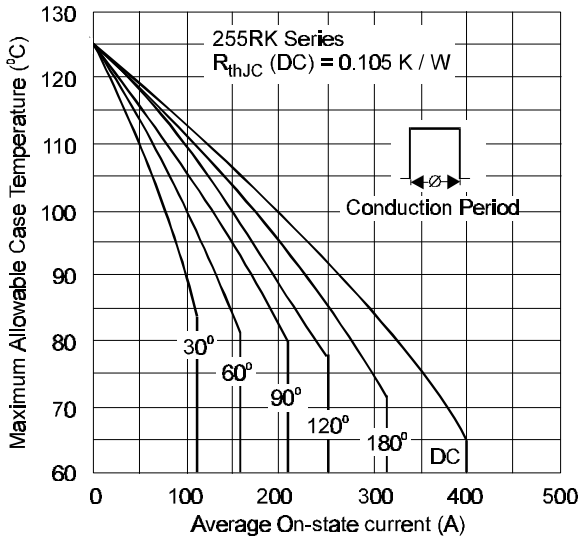

Fig. 2 - Current Ratings Characteristics

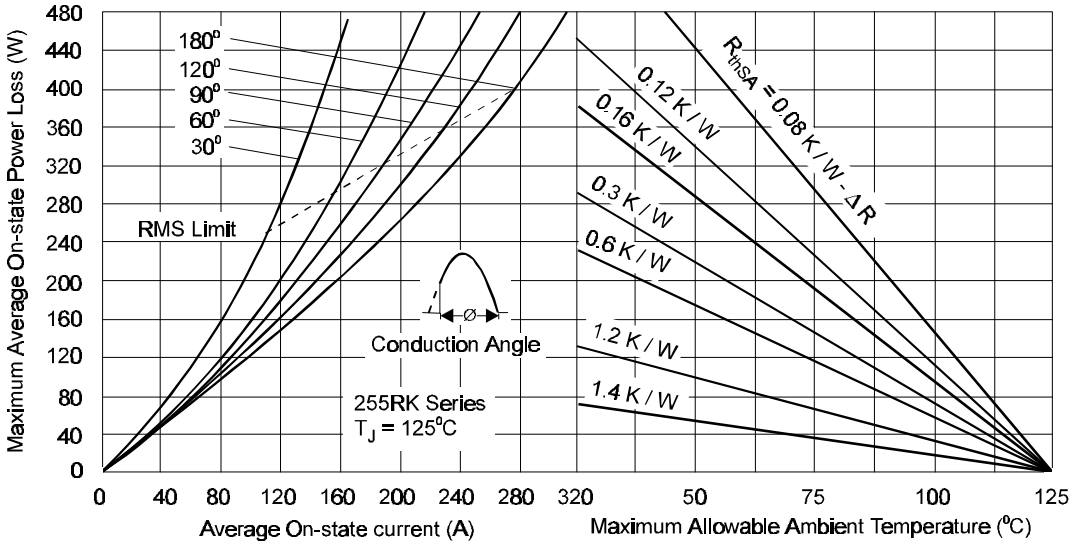

Fig. 3 - On-state Power Loss Characteristics

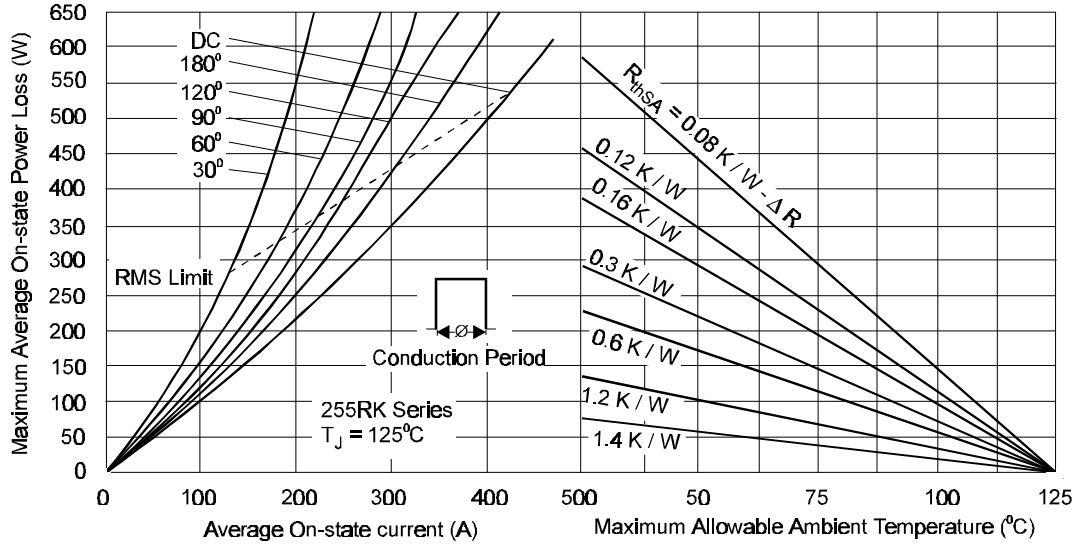

Fig. 4 - On-state Power Loss Characteristics

255RK SERIES

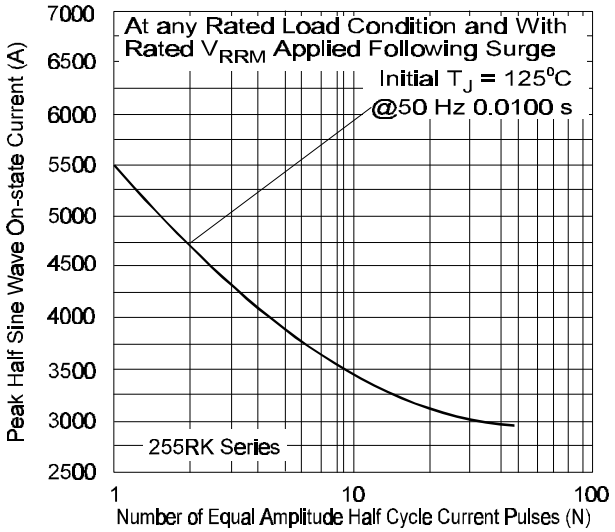

Fig. 5 - Maximum Non-Repetitive Surge Current

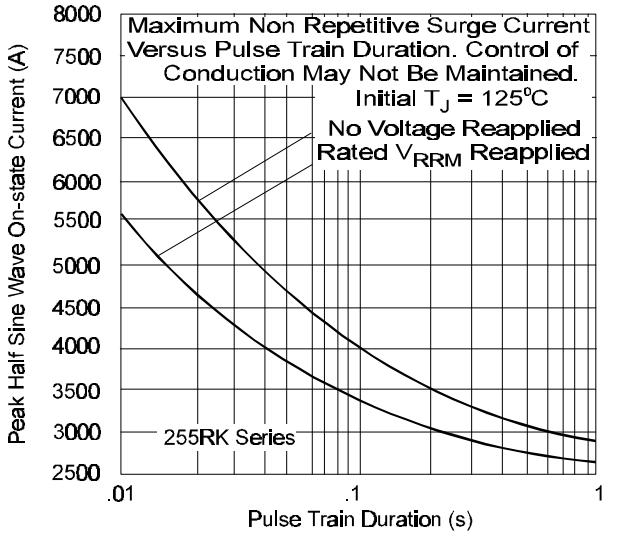

Fig. 6 - Maximum Non-Repetitive Surge Current

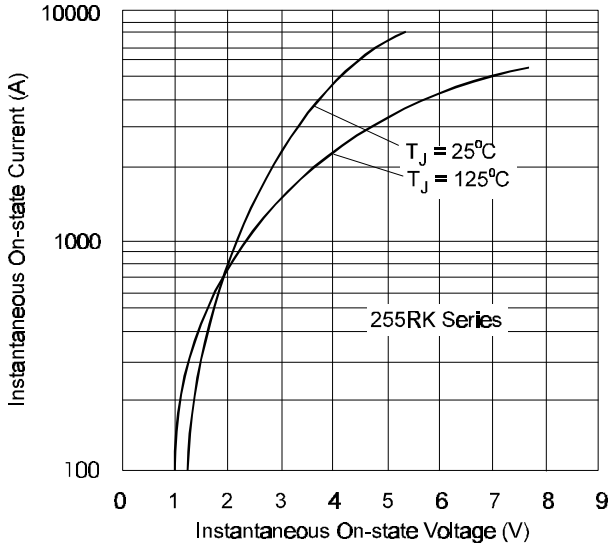

Fig. 7 - On-state Voltage Drop Characteristics

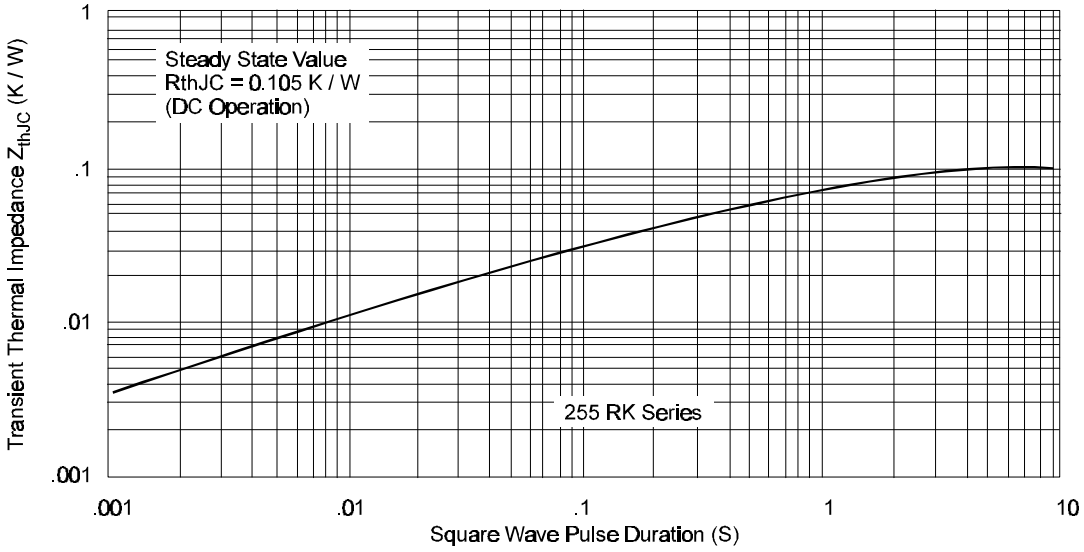

Fig. 8 - Thermal Impedance Z_{thJC} Characteristics

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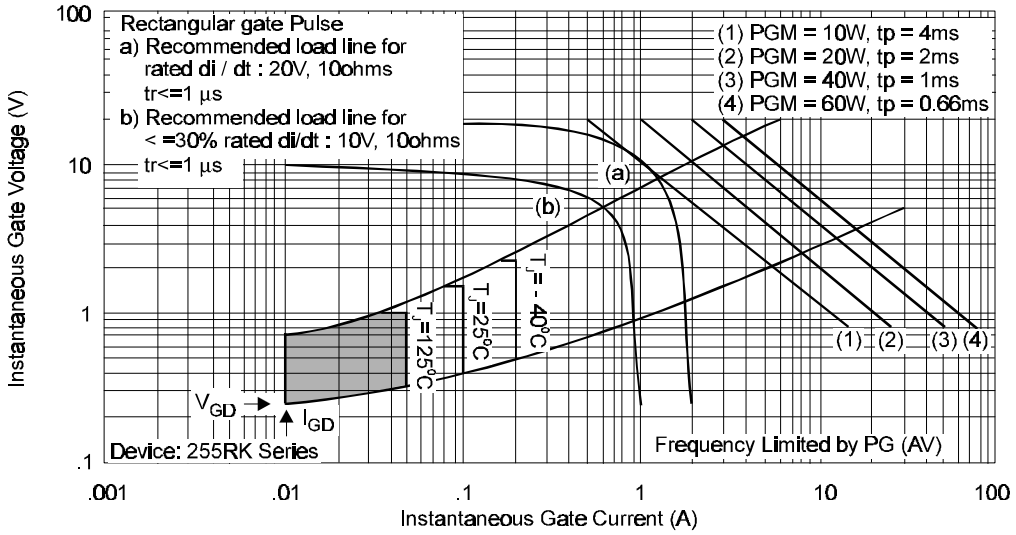

Fig. 9 - Gate Characteristics

Last Update : Feb. 2006